MDMA50P1200TG

Standard Rectifier Module

V_{RRM}	<i>=</i> 2x 1200 V			
I _{fav}	=	50 A		
VF	=	1.09 V		

Phase leg

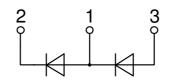
Part number

MDMA50P1200TG



Backside: isolated **E**72873

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Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- · Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase
- bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- · Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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MDMA50P1200TG

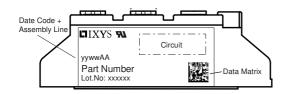
Rectifier	r				Rating	s	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			1300	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I _R	reverse current	$V_{R} = 1200 V$	$T_{VJ} = 25^{\circ}C$			50	μA
		$V_{R} = 1200 V$	$T_{vJ} = 150^{\circ}C$			1.5	mA
V _F	forward voltage drop	I _F = 50 A	$T_{VJ} = 25^{\circ}C$			1.13	V
		I _F = 100 A				1.34	V
		$I_{\rm F} = 50 {\rm A}$	T _{vJ} = 125 °C			1.09	۷
		$I_{F} = 100 \text{ A}$				1.37	V
FAV	average forward current	T _c = 100°C	$T_{VJ} = 150 ^{\circ}\text{C}$			50	Α
		rectangular d = 0.5					1
V _{F0}	threshold voltage		$T_{VJ} = 150^{\circ}C$			0.80	V
r _F	slope resistance } for power	loss calculation only				5.7	mΩ
\mathbf{R}_{thJC}	thermal resistance junction to ca	ase				0.65	K/W
R thCH	thermal resistance case to heats	sink			0.20		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			190	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			850	Α
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			920	Α
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 150^{\circ}C$			725	Α
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			780	Α
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			3.62	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			3.52	kA²s
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 150^{\circ}C$			2.63	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			2.53	kA²s
C	junction capacitance	$V_{R} = 400 \text{ V}; \text{ f} = 1 \text{ MHz}$	$T_{vJ} = 25^{\circ}C$		27		pF

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Package TO-240AA				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					200	Α
T _{vj}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						76		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	creenade distance on surfa	ce striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on suna	ce striking distance through an	terminal to backside	16.0	16.0			mm
V	<i>isolation voltage</i> t = 1 second t = 1 minute			4800			V	
		t = 1 minute	50/60 Hz, RMS; lıso∟ ≤ 1 mA	4000			V	



Part description

M = Module

D = Diode M = Standard Rectifier

A = (up to 1800V) 50 = Current Rating [A]

P = Phase leg 1200 = Reverse Voltage [V] TG = TO-240AA

[Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	MDMA50P1200TG	MDMA50P1200TG	Box	36	513029

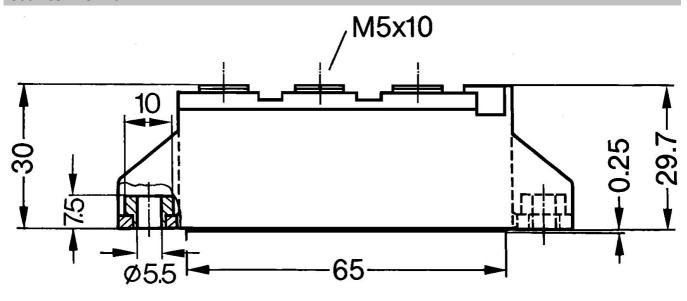
Equiva	alent Circuits for	Simulation	* on die level	T _{vj} = 150 °C
)R	Rectifier		
V _{0 max}	threshold voltage	0.8		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	4.5		mΩ

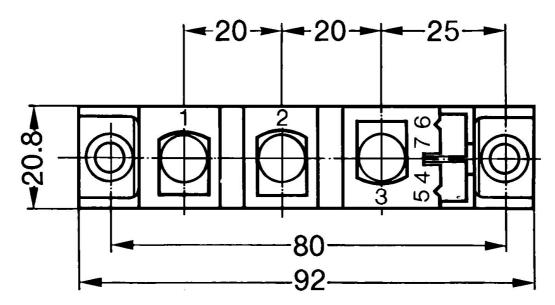
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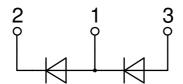
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MDMA50P1200TG

Outlines TO-240AA







MDMA50P1200TG

150

2

50

100

T_c [°C]

case temperature per diode

t_i (s)

0.001

0.010

0.060

0.270

3

t [ms]

4 5 6 7 8 10

DC =

1

0.5

0.4

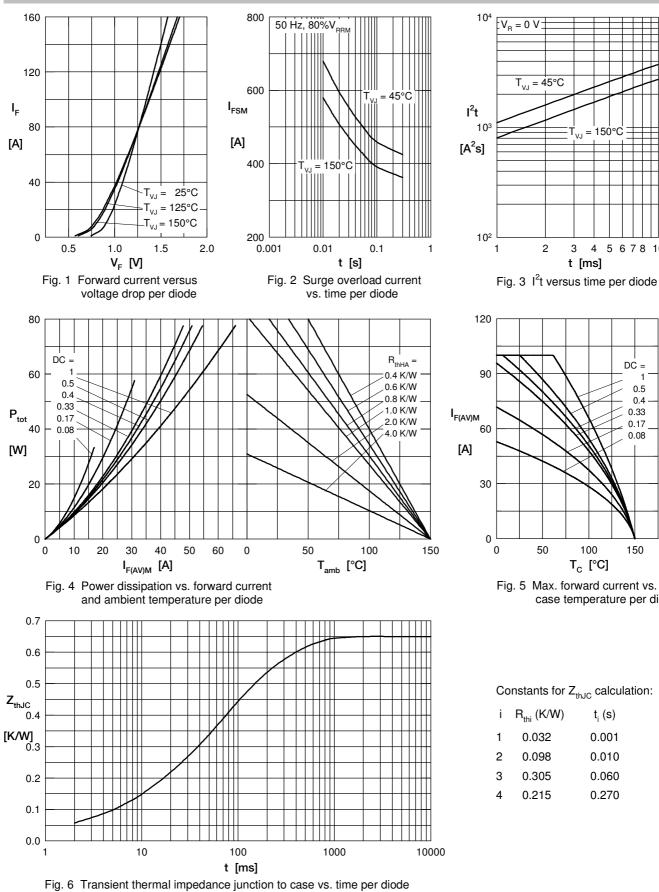
0.33

0.17

0.08

150

Rectifier





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